

SOT-23 Plastic-Encapsulate DIODE

Features

• Power dissipation

 P_D : 150 mW ($T_{amb}=25^{\circ}C$)

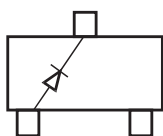
• Forward Current

 I_F : 100 mA

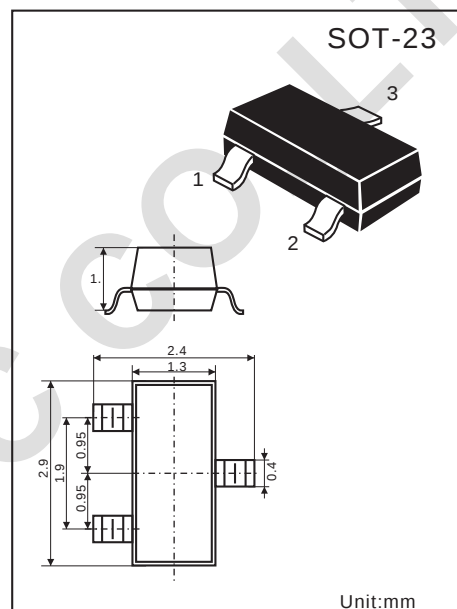
• Reverse Voltage

 V_R : 80V

• Operating and storage junction temperature range

 T_j, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$ 

Marking:F3



ELECTRICAL CHARACTERISTICS

(Ta=25°C unless otherwise specified)

Parameter	Symbol	Test Condition	MIN.	MAX.	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	80		V
Reverse Voltage leakage current	I_R	$V_R=80V$		0.5	μA
Forward Voltage	V_F	$I_F=100mA$		1.2	V
Diode Capacitance	C_{tot}	$V_R=0V$ $f=1MHz$		3	pF
Reverse Recovery Time	t_{rr}	$I_F=I_R=10mA$ $I_{rr}=0.1I_R$		4	nS

Typical Characteristics

